

# **ISC Silicon NPN Power Transistor**

KTD2060

### **DESCRIPTION**

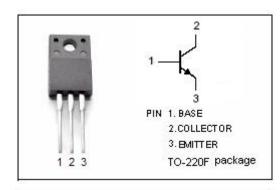
- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 80V(Min)
- · Collector Power Dissipation-
  - : P<sub>C</sub>= 25W@ T<sub>C</sub>= 25℃
- · Low Collector Saturation Voltage-
  - :  $V_{CE(sat)}$ = 1.5V(Max)@ ( $I_{C}$ = 3A,  $I_{B}$ = 0.3A)
- Complement to Type KTB1368
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

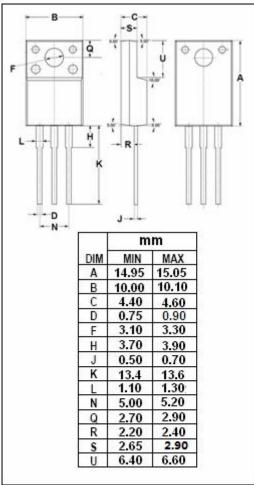


· Designed for general purpose applications.

# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	80	V
V <sub>CEO</sub>	Collector-Emitter Voltage	80	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
lc	Collector Current-Continuous	4	Α
I <sub>B</sub>	Base Current-Continuous	0.4	А
Pc	Collector Power Dissipation @T <sub>C</sub> =25°C	25	W
TJ	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature	-55~150	$^{\circ}$







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#### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	80			V
V <sub>(BR)EBO</sub>	Emitter –Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>B</sub> = 0	5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.3A			1.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 3A; V <sub>CE</sub> = 5V			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 80V; I <sub>E</sub> = 0			30	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			100	μА
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V	40		240	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 5V	15			
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1MHz		90		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V		8		MHz

### ♦ h<sub>FE-1</sub> Classifications

R	0	Y
40-80	70-140	120-240

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